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# P-Channel 1.8 V (G-S) MOSFET

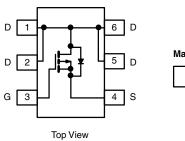
| PRODUCT SUMMARY     |                                    |                    |  |  |
|---------------------|------------------------------------|--------------------|--|--|
| V <sub>DS</sub> (V) | $R_{DS(on)}(\Omega)$               | I <sub>D</sub> (A) |  |  |
| - 20                | 0.195 at V <sub>GS</sub> = - 4.5 V | - 0.84             |  |  |
|                     | 0.260 at V <sub>GS</sub> = - 2.5 V | - 0.73             |  |  |
|                     | 0.350 at V <sub>GS</sub> = - 1.8 V | - 0.64             |  |  |

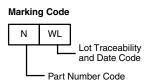
### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Low Threshold
- Smallest LITTLE FOOT<sup>®</sup> Package: 1.6 mm x 1.6 mm
- Low 0.6 mm Profile
- Compliant to RoHS Directive 2002/95/EC



#### SC-89 (6-LEADS)





Ordering Information: Si1037X-T1-GE3 (Lead (Pb)-free and Halogen-free)

### **APPLICATIONS**

- Cell Phones and Pagers
  - Load Switch
- · Battery Operated Systems

| <b>ABSOLUTE MAXIMUM RATINGS</b> (T                              | $_{A}$ = 25 °C, unle   | ess otherwise                     | noted)      |              |      |  |
|---|------------------------|-----------------------------------|-------------|--------------|------|--|
| Parameter   |                        | Symbol                            | 5 s         | Steady State | Unit |  |
| Drain-Source Voltage  |                        | V <sub>DS</sub>                   | - 20        |              | V    |  |
| Gate-Source Voltage   |                        | V <sub>GS</sub>                   | ± 8         |              |      |  |
| Continuous Drain Current /T 150 °C\2                            | T <sub>A</sub> = 25 °C | - I <sub>D</sub>                  | - 0.84      | - 0.77       |      |  |
| Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup> | T <sub>A</sub> = 70 °C |                                   | - 0.68      | - 0.62       | ۸    |  |
| Pulsed Drain Current  |                        | I <sub>DM</sub>                   | - 4         |              | Α    |  |
| Continuous Diode Current (Diode Conduction) <sup>a</sup>        |                        | I <sub>S</sub>                    | - 0.18      | - 0.14       |      |  |
| Manipular Brown Birelandian                                     | T <sub>A</sub> = 25 °C | P <sub>D</sub>                    | 0.21        | 0.17         | W    |  |
| Maximum Power Dissipation <sup>a</sup>                          | T <sub>A</sub> = 70 °C |                                   | 0.13        | 0.10         | VV   |  |
| Operating Junction and Storage Temperature Range                |                        | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150 |              | °C   |  |

| THERMAL RESISTANCE RATINGS               |              |                     |         |         |      |  |
|--|--------------|---------------------|---------|---------|------|--|
| Parameter                                |              | Symbol              | Typical | Maximum | Unit |  |
| Maximum Junction-to-Ambient <sup>a</sup> | t ≤ 5 s      | - R <sub>thJA</sub> | 500     | 600     | °C/W |  |
|  | Steady State |                     | 600     | 720     |      |  |

#### Notes

a. Surface mounted on 1" x 1" FR4 board with minimum copper.

# Vishay Siliconix



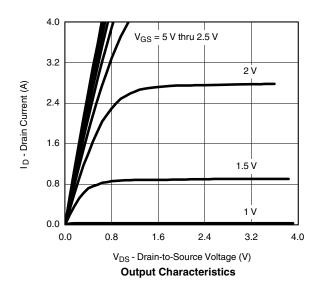
| Parameter                                     | Symbol              | Test Conditions  | Min.   | Тур.   | Max.  | Unit |  |
|---|---------------------|--|--------|--------|-------|------|--|
| Static  |                     |  |        |        |       |      |  |
| Gate Threshold Voltage                        | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$                                      | - 0.45 |        |       | V    |  |
| Gate-Body Leakage                             | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$                           |        |        | ± 100 | nA   |  |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>    | V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V                            | - 1    |        |       |      |  |
|   |                     | V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C    |        |        | - 5   | μΑ   |  |
| On-State Drain Current <sup>a</sup>           | I <sub>D(on)</sub>  | V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 4.5 V                         | - 4    |        |       | Α    |  |
|   |                     | V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 0.77 A                       |        | 0.160  | 0.195 | 50 Ω |  |
| Drain-Source On-State Resistance <sup>a</sup> | R <sub>DS(on)</sub> | V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 0.67 A                       |        | 0.212  | 0.260 |      |  |
|   |                     | V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 0.2 A                        |        | 0.290  | 0.350 |      |  |
| Forward Transconductance <sup>a</sup>         | 9 <sub>fs</sub>     | V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 0.77 A                        |        | 3.1    |       | S    |  |
| Diode Forward Voltage <sup>a</sup>            | $V_{SD}$            | I <sub>S</sub> = - 0.14 A, V <sub>GS</sub> = 0 V                           |        | - 0.78 | - 1.2 | V    |  |
| Dynamic <sup>b</sup>                          |                     |  |        |        |       |      |  |
| Total Gate Charge                             | $Q_g$               |  |        | 3.5    | 5.5   |      |  |
| Gate-Source Charge                            | $Q_{gs}$            | $V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -0.77 \text{ A}$ |        | 0.65   |       | nC   |  |
| Gate-Drain Charge                             | $Q_{gd}$            |  |        | 0.60   |       |      |  |
| Turn-On Delay Time                            | t <sub>d(on)</sub>  |  |        | 10     | 20    |      |  |
| Rise Time                                     | t <sub>r</sub>      | $V_{DD}$ = - 10 V, $R_L$ = 20 $\Omega$                                     |        | 15     | 30    |      |  |
| Turn-Off Delay Time                           | t <sub>d(off)</sub> | $I_{D} \cong -0.5 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_{G} = 6 \Omega$   |        | 30     | 60    | ns   |  |
| Fall Time                                     | t <sub>f</sub>      |  |        | 10     | 20    |      |  |
| Source-Drain Reverse Recovery Time            | t <sub>rr</sub>     | I <sub>F</sub> = - 0.14 A, dl/dt = 100 A/μs                                |        | 20     | 40    |      |  |

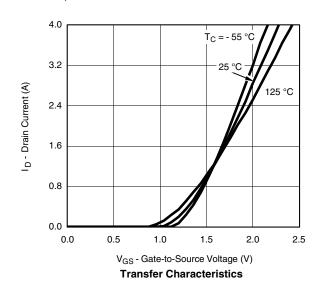
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

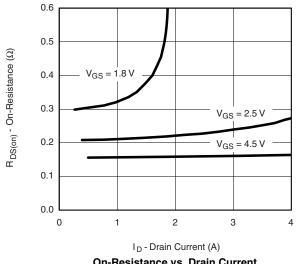




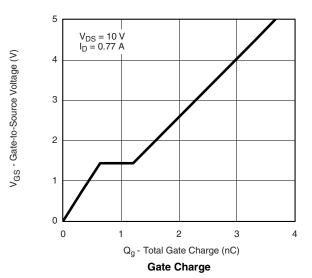


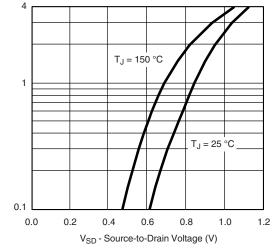


## **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)

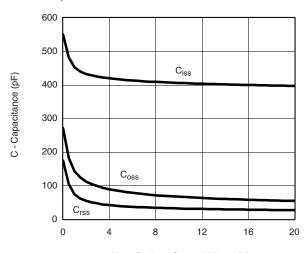


#### On-Resistance vs. Drain Current



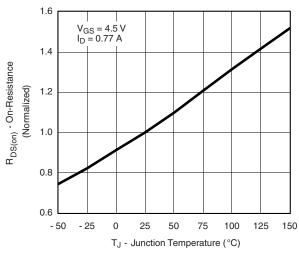


Source-Drain Diode Forward Voltage

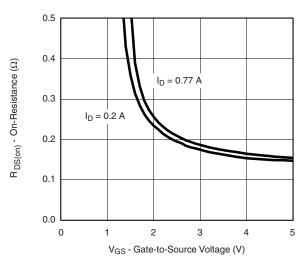


V<sub>DS</sub> - Drain-to-Source Voltage (V)

#### Capacitance



On-Resistance vs. Junction Temperature



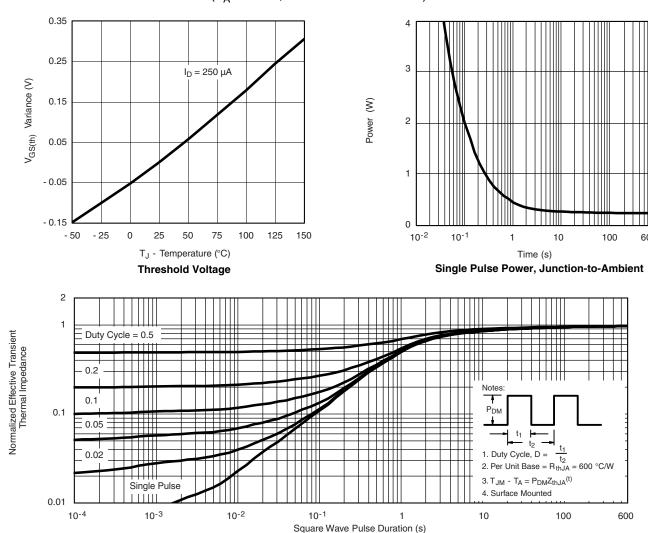
On-Resistance vs. Gate-to-Source Voltage

Is - Source Current (A)

# Vishay Siliconix



## **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

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